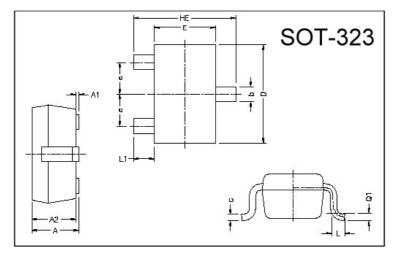
GS411SD

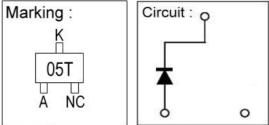
SURFACE MOUNT, SCHOTTKY BARRIER DIODE **VOLTAGE 40V, CURRENT 0.5A**

Description

The GS411SD is designed for low power rectification.

Package Dimensions





REF.	Milli	meter	REF.	Millimeter					
	Min.	Max.	nLI.	Min.	Max.				
Α	0.80	1.10	L1	0.42 REF.					
A1	0	0.10	L	0.15	0.35				
A2	0.80	1.00	b	0.25	0.40				
D	1.80	2.20	С	0.10	0.25				
Е	1.15	1.35	е	0.65 REF.					
HE	1.80	2.40	Q1	0.15 BSC.					

Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit	
Junction Temperature	Tj	+125	$^{\circ}$	
Storage Temperature	Tstg	-40 ~ +125	$^{\circ}$ C	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V	
Maximum RMS Voltage	V_{RMS}	28	V	
Maximum DC Blocking Voltage	V_{DC}	20	V	
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	Α	
Typical Junction Capacitance between Terminal (Note 1)	CJ	20	pF	
Maximum Average Forward Rectified Current	lo	0.5	Α	
Total Power Dissipation	PD	225	mW	

Electrical Characteristics (at TA = 25°C unless otherwise noted)

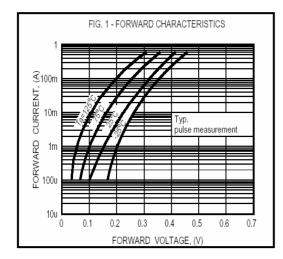
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions				
Reverse Breakdown Voltage	V(BR)R	40	-	-	V	IR=100μA				
Maximum Instantaneous Forward Voltage	VF	1	-	300	mV	IF1=10mA				
Maximum instantaneous i orward voitage		-	-	500		IF2=500mA				
Maximum Average Reverse Current	lr	-	-	30	uA	VR=10V				

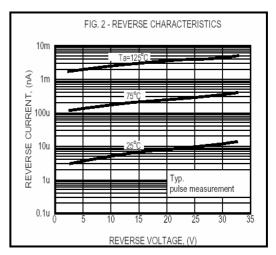
Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

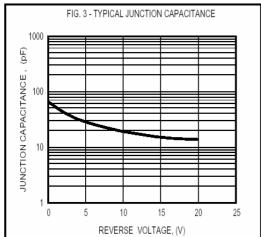
2. ESD sensitive product handling required.

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Characteristics Curve







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